

(4)

- (b) Convert the following decimal numbers to binary. 4

89 , 75.66

- (c) Convert the following binary numbers to decimal: 4

1011 , 1101.1011

- (d) Why is NAND gate called universal logic gate. Construct OR gate using NAND gate. 4

UNIT - V

9. (a) What is modulation? Why is modulation necessary in communication system? 7
- (b) Define amplitude modulation. Show that an amplitude modulation wave can be represented by a carrier and two sideband frequencies for each frequency of modulation. 7
10. (a) Why does amplitude modulation give noisy reception? 3
- (b) What is frequency modulation? Distinguish between amplitude and frequency modulation. 7
- (c) Derive the expression for the FM voltage wave. 4

2023/EVEN/08/21/PHY-203C/064

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PG (CBCS) EVEN SEMESTER EXAMINATION, 2023

PHYSICS

2nd Semester

Course No. : PHYCC - 203 C

(Electronic Devices and Circuits)

Full Marks : 70

Pass Marks : 28

Time : 3 hours

The figures in the margin indicate full marks for the questions

(Answer five questions, taking one from each unit)

UNIT - I

1. (a) What is an intrinsic semiconductor? Describe briefly how p-type and n-type semiconductors are developed from pure silicon. 7
- (b) State the differences among a metal, a semiconductor and an insulator with the help of band theory of solids. 7
2. (a) What is a semiconductor? Discuss some important properties of semiconductor. 7
- (b) What is the need of adding impurity to an intrinsic semiconductor? 2

(Turn Over)

(2)

- (c) What is the effect of temperature on extrinsic semiconductor? 2
- (d) What are an electron and a hole? How is a hole created? 3

UNIT - II

3. (a) What is a P-N junction diode? Explain the formation of the depletion region in a P - N junction diode. 7
- (b) Explain the construction and working of an n-p-n transistor. 7
4. (a) Explain the current-voltage (I-V) characteristics of a p-n junction diode under forward and reverse bias mode. 7
- (b) What is a Zener diode? What is the avalanche breakdown in Zener diode? 2+2=4
- (c) What is thermal runaway? How is it minimized? 3

UNIT - III

5. (a) Explain the working of a half-wave rectifier. Give proper circuit diagram. 7

(3)

- (b) Show that the maximum rectifier efficiency of half-wave recitifier is 40.6%. 5
- (c) What is the ripple factor of a half-wave rectifier? 2

6. (a) State the Barkhausen criteria for sustained oscillation. 2
- (b) What are the essential components of a transistor oscillator? What is the difference between amplifer and oscillator? 5
- (c) Give the construction and working of a bridge-type rectifier. 7

UNIT - IV

7. (a) Simplify the following Boolean expressions:
(i) $Y = AB + A(B+C) + B(B+C)$ 4x2=8
(ii) $Y = AB + ABC + \bar{A}B + A\bar{B}C$
(iii) $Y = (A + B)(A + \bar{B})(\bar{A} + \bar{B})$
(iv) $Y = (A + B + C)(A + B)$
- (b) Explain how we realise OR gate in Lab with diodes. Also write the Boolean expression and truth table. 6
8. (a) State De-Morgan's theorem. 2

(Turn Over)